

AN79Nxx Series

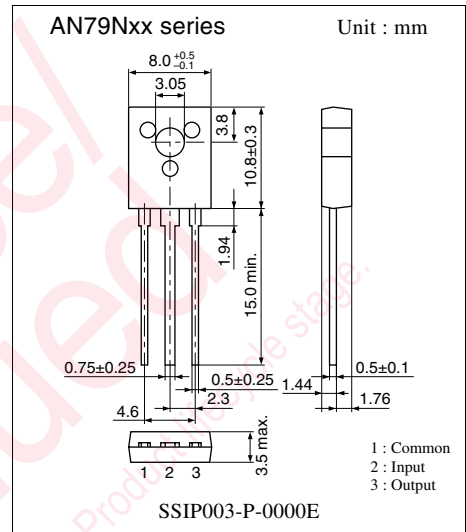
3-pin negative output voltage regulator (300 mA type)

■ Overview

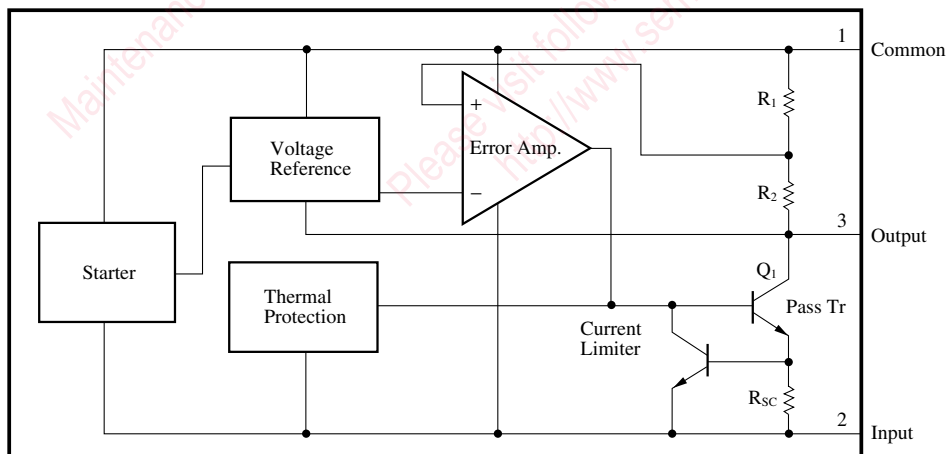
The AN79Nxx series is a 3-pin, fixed negative output type monolithic voltage regulator. Stabilized fixed output voltage is obtained from unstable DC input voltage without using any external component IC. 12 types of output voltage are available: -4V , -5V , -6V , -7V , -8V , -9V , -10V , -12V , -15V , -18V , -20V and -24V . They can be used widely in power circuits with current capacity of up to 300mA.

■ Features

- No external components
- Output voltage: -4V , -5V , -6V , -7V , -8V , -9V , -10V , -12V , -15V , -18V , -20V , -24V
- Built-in overcurrent limit circuit
- Built-in thermal overload protection circuit
- Built-in ASO (area of safe operation) protection circuit



■ Block Diagram



■ Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Input voltage	V_i	-35 *1	V
		-40 *2	V
Power dissipation	P_D	8 *3	W
Operating ambient temperature	T_{opr}	-20 to +80	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

*1 AN79N04, AN79N05, AN79N06, AN79N07, AN79N08, AN79N09, AN79N10, AN79N12, AN79N15, AN79N18

*2 AN79N20, AN79N24

*3 Follow the derating curve. When T_j exceeds 150°C , the internal circuit cuts off the output.

■ Electrical Characteristics at $T_a = 25^\circ\text{C}$

• AN79N04 (-4V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	-3.84	-4	-4.16	V
Output voltage tolerance	V_O	$V_i = -6$ to -25V , $I_O = 5$ to 200mA	-3.8	—	-4.2	V
Line regulation	REG_{IN}	$V_i = -6$ to -25V , $T_j = 25^\circ\text{C}$	—	9	40	mV
		$V_i = -7$ to -17V , $T_j = 25^\circ\text{C}$	—	4	20	mV
Load regulation	REG_L	$I_O = 1$ to 300mA , $T_j = 25^\circ\text{C}$	—	20	80	mV
		$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	10	40	mV
Bias current	I_{Bias}	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_i = -7$ to -25V , $T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	100	—	μV
Ripple rejection ratio	RR	$V_i = -7$ to -17V , $I_O = 50\text{mA}$, $f = 120\text{Hz}$	60	—	—	dB
Minimum input/output voltage difference	$V_{DIF(min)}$	$I_O = 200\text{mA}$, $T_j = 25^\circ\text{C}$	—	1.1	—	V
Output short-circuit current	$I_{O(Short)}$	$V_i = -35\text{V}$, $T_j = 25^\circ\text{C}$	—	10	—	mA
Peak output current	$I_{O(Peak)}$	$T_j = 25^\circ\text{C}$	—	500	—	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5\text{mA}$	—	-0.4	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_i = -9\text{V}$, $I_O = 100\text{mA}$, $C_1 = 2\mu\text{F}$, $C_O = 1\mu\text{F}$ and $T_j = 0$ to 125°C

■ Electrical Characteristics at $T_a = 25^\circ\text{C}$ (continued)

• AN79N05 (–5V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	–4.8	–5	–5.2	V
Output voltage tolerance	V_O	$V_I = -7$ to -25V , $I_O = 5$ to 200mA	–4.75	—	–5.25	V
Line regulation	REG_{IN}	$V_I = -7$ to -25V , $T_j = 25^\circ\text{C}$	—	10	50	mV
		$V_I = -8$ to -18V , $T_j = 25^\circ\text{C}$	—	5	30	mV
Load regulation	REG_{L}	$I_O = 1$ to 300mA , $T_j = 25^\circ\text{C}$	—	20	100	mV
		$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	10	50	mV
Bias current	I_{Bias}	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias(IN)}}$	$V_I = -8$ to -25V , $T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias(L)}}$	$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	125	—	μV
Ripple rejection ratio	RR	$V_I = -8$ to -18V , $I_O = 50\text{mA}$, $f = 120\text{Hz}$	60	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$I_O = 200\text{mA}$, $T_j = 25^\circ\text{C}$	—	1.1	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_I = -35\text{V}$, $T_j = 25^\circ\text{C}$	—	10	—	mA
Peak output current	$I_{\text{O(Peak)}}$	$T_j = 25^\circ\text{C}$	—	500	—	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5\text{mA}$	—	–0.4	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = -10\text{V}$, $I_O = 100\text{mA}$, $C_1 = 2\mu\text{F}$, $C_O = 1\mu\text{F}$ and $T_j = 0$ to 125°C

• AN79N06 (–6V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	–5.75	–6	–6.25	V
Output voltage tolerance	V_O	$V_I = -8$ to -25V , $I_O = 5$ to 200mA	–5.7	—	–6.3	V
Line regulation	REG_{IN}	$V_I = -8$ to -25V , $T_j = 25^\circ\text{C}$	—	11	60	mV
		$V_I = -9$ to -19V , $T_j = 25^\circ\text{C}$	—	6	40	mV
Load regulation	REG_{L}	$I_O = 1$ to 300mA , $T_j = 25^\circ\text{C}$	—	20	120	mV
		$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	10	60	mV
Bias current	I_{Bias}	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias(IN)}}$	$V_I = -9$ to -25V , $T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias(L)}}$	$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	150	—	μV
Ripple rejection ratio	RR	$V_I = -9$ to -19V , $I_O = 50\text{mA}$, $f = 120\text{Hz}$	60	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$I_O = 5\text{mA}$, $T_j = 0$ to 125°C	—	1.1	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_I = -35\text{V}$, $T_j = 25^\circ\text{C}$	—	10	—	mA
Peak output current	$I_{\text{O(Peak)}}$	$T_j = 25^\circ\text{C}$	—	500	—	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 200\text{mA}$	—	–0.4	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = -11\text{V}$, $I_O = 100\text{mA}$, $C_1 = 2\mu\text{F}$, $C_O = 1\mu\text{F}$ and $T_j = 0$ to 125°C

■ Electrical Characteristics at $T_a = 25^\circ\text{C}$ (continued)

• AN79N07 (–7V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	–6.7	–7	–7.3	V
Output voltage tolerance	V_O	$V_I = -9$ to -25V , $I_O = 5$ to 200mA	–6.65	—	–7.35	V
Line regulation	REG_{IN}	$V_I = -9$ to -25V , $T_j = 25^\circ\text{C}$	—	12	70	mV
		$V_I = -10$ to -20V , $T_j = 25^\circ\text{C}$	—	7	35	mV
Load regulation	REG_{L}	$I_O = 1$ to 300mA , $T_j = 25^\circ\text{C}$	—	20	140	mV
		$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	10	70	mV
Bias current	I_{Bias}	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias(IN)}}$	$V_I = -10$ to -25V , $T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias(L)}}$	$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	175	—	μV
Ripple rejection ratio	RR	$V_I = -10$ to -20V , $I_O = 50\text{mA}$, $f = 120\text{Hz}$	59	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$I_O = 200\text{mA}$, $T_j = 25^\circ\text{C}$	—	1.1	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_I = -35\text{V}$, $T_j = 25^\circ\text{C}$	—	10	—	mA
Peak output current	$I_{\text{O(Peak)}}$	$T_j = 25^\circ\text{C}$	—	500	—	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5\text{mA}$	—	–0.5	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = -12\text{V}$, $I_O = 100\text{mA}$, $C_1 = 2\mu\text{F}$, $C_O = 1\mu\text{F}$ and $T_j = 0$ to 125°C

• AN79N08 (–8V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	–7.7	–8	–8.3	V
Output voltage tolerance	V_O	$V_I = -10.5$ to -25V , $I_O = 5$ to 200mA	–7.6	—	–8.4	V
Line regulation	REG_{IN}	$V_I = -10.5$ to -25V , $T_j = 25^\circ\text{C}$	—	13	80	mV
		$V_I = -11$ to -21V , $T_j = 25^\circ\text{C}$	—	8	40	mV
Load regulation	REG_{L}	$I_O = 1$ to 300mA , $T_j = 25^\circ\text{C}$	—	25	160	mV
		$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	10	80	mV
Bias current	I_{Bias}	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias(IN)}}$	$V_I = -10.5$ to -25V , $T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias(L)}}$	$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	200	—	μV
Ripple rejection ratio	RR	$V_I = -11.5$ to -21.5V , $I_O = 50\text{mA}$, $f = 120\text{Hz}$	59	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$I_O = 200\text{mA}$, $T_j = 25^\circ\text{C}$	—	1.1	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_I = -35\text{V}$, $T_j = 25^\circ\text{C}$	—	10	—	mA
Peak output current	$I_{\text{O(Peak)}}$	$T_j = 25^\circ\text{C}$	—	500	—	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5\text{mA}$	—	–0.6	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = -14\text{V}$, $I_O = 100\text{mA}$, $C_1 = 2\mu\text{F}$, $C_O = 1\mu\text{F}$ and $T_j = 0$ to 125°C

■ Electrical Characteristics at $T_a = 25^\circ\text{C}$ (continued)

• AN79N09 (–9V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	–8.65	–9	–9.35	V
Output voltage tolerance	V_O	$V_I = -11.5$ to -26V , $I_O = 5$ to 200mA	–8.55	—	–9.45	V
Line regulation	REG_{IN}	$V_I = -11.5$ to -26V , $T_j = 25^\circ\text{C}$	—	14	80	mV
		$V_I = -12$ to -22V , $T_j = 25^\circ\text{C}$	—	9	50	mV
Load regulation	REG_{L}	$I_O = 1$ to 300mA , $T_j = 25^\circ\text{C}$	—	25	180	mV
		$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	10	90	mV
Bias current	I_{Bias}	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias(IN)}}$	$V_I = -11.5$ to -26V , $T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias(L)}}$	$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	225	—	μV
Ripple rejection ratio	RR	$V_I = -12$ to -22V , $I_O = 50\text{mA}$, $f = 120\text{Hz}$	58	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$I_O = 200\text{mA}$, $T_j = 25^\circ\text{C}$	—	1.1	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_I = -35\text{V}$, $T_j = 25^\circ\text{C}$	—	10	—	mA
Peak output current	$I_{\text{O(Peak)}}$	$T_j = 25^\circ\text{C}$	—	500	—	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5\text{mA}$	—	–0.6	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = -15\text{V}$, $I_O = 100\text{mA}$, $C_1 = 2\mu\text{F}$, $C_O = 1\mu\text{F}$ and $T_j = 0$ to 125°C

• AN79N10 (–10V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	–9.6	–10	–10.4	V
Output voltage tolerance	V_O	$V_I = -12.5$ to -27V , $I_O = 5$ to 200mA	–9.5	—	–10.5	V
Line regulation	REG_{IN}	$V_I = -12.5$ to -27V , $T_j = 25^\circ\text{C}$	—	15	80	mV
		$V_I = -13$ to -23V , $T_j = 25^\circ\text{C}$	—	10	50	mV
Load regulation	REG_{L}	$I_O = 1$ to 300mA , $T_j = 25^\circ\text{C}$	—	25	200	mV
		$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	10	100	mV
Bias current	I_{Bias}	$T_j = 25^\circ\text{C}$	—	3.0	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias(IN)}}$	$V_I = -12.5$ to -27V , $T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias(L)}}$	$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	250	—	μV
Ripple rejection ratio	RR	$V_I = -13$ to -23V , $I_O = 50\text{mA}$, $f = 120\text{Hz}$	58	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$I_O = 200\text{mA}$, $T_j = 25^\circ\text{C}$	—	1.1	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_I = -35\text{V}$, $T_j = 25^\circ\text{C}$	—	10	—	mA
Peak output current	$I_{\text{O(Peak)}}$	$T_j = 25^\circ\text{C}$	—	500	—	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5\text{mA}$	—	–0.7	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = -16\text{V}$, $I_O = 100\text{mA}$, $C_1 = 2\mu\text{F}$, $C_O = 1\mu\text{F}$ and $T_j = 0$ to 125°C

■ Electrical Characteristics at $T_a = 25^\circ\text{C}$ (continued)

• AN79N12 (–12V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	–11.5	–12	–12.5	V
Output voltage tolerance	V_O	$V_I = -14.5$ to -30V , $I_O = 5$ to 200mA	–11.4	—	–12.6	V
Line regulation	REG_{IN}	$V_I = -14.5$ to -30V , $T_j = 25^\circ\text{C}$	—	15	80	mV
		$V_I = -15$ to -25V , $T_j = 25^\circ\text{C}$	—	10	50	mV
Load regulation	REG_{L}	$I_O = 1$ to 300mA , $T_j = 25^\circ\text{C}$	—	25	240	mV
		$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	10	120	mV
Bias current	I_{Bias}	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias(IN)}}$	$V_I = -14.5$ to -30V , $T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias(L)}}$	$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	300	—	μV
Ripple rejection ratio	RR	$V_I = -15$ to -25V , $I_O = 50\text{mA}$, $f = 120\text{Hz}$	57	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$I_O = 200\text{mA}$, $T_j = 25^\circ\text{C}$	—	1.1	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_I = -35\text{V}$, $T_j = 25^\circ\text{C}$	—	10	—	mA
Peak output current	$I_{\text{O(Peak)}}$	$T_j = 25^\circ\text{C}$	—	500	—	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5\text{mA}$	—	–0.8	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = -19\text{V}$, $I_O = 100\text{mA}$, $C_1 = 2\mu\text{F}$, $C_O = 1\mu\text{F}$ and $T_j = 0$ to 125°C

• AN79N15 (–15V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	–14.4	–15	–15.6	V
Output voltage tolerance	V_O	$V_I = -17.5$ to -30V , $I_O = 5$ to 200mA	–14.25	—	–15.75	V
Line regulation	REG_{IN}	$V_I = -17.5$ to -30V , $T_j = 25^\circ\text{C}$	—	16	80	mV
		$V_I = -18$ to -28V , $T_j = 25^\circ\text{C}$	—	11	50	mV
Load regulation	REG_{L}	$I_O = 1$ to 300mA , $T_j = 25^\circ\text{C}$	—	25	240	mV
		$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	10	120	mV
Bias current	I_{Bias}	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias(IN)}}$	$V_I = -17.5$ to -30V , $T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias(L)}}$	$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	375	—	μV
Ripple rejection ratio	RR	$V_I = -18$ to -28V , $I_O = 50\text{mA}$, $f = 120\text{Hz}$	56	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$I_O = 200\text{mA}$, $T_j = 25^\circ\text{C}$	—	1.1	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_I = -35\text{V}$, $T_j = 25^\circ\text{C}$	—	10	—	mA
Peak output current	$I_{\text{O(Peak)}}$	$T_j = 25^\circ\text{C}$	—	500	—	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5\text{mA}$	—	–0.9	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = -23\text{V}$, $I_O = 100\text{mA}$, $C_1 = 2\mu\text{F}$, $C_O = 1\mu\text{F}$ and $T_j = 0$ to 125°C

■ Electrical Characteristics at $T_a = 25^\circ\text{C}$ (continued)

• AN79N18 (–18V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	–17.3	–18	–18.7	V
Output voltage tolerance	V_O	$V_I = -21$ to -33V , $I_O = 5$ to 200mA	–17.1	—	–18.9	V
Line regulation	REG_{IN}	$V_I = -21$ to -33V , $T_j = 25^\circ\text{C}$	—	18	80	mV
		$V_I = -22$ to -32V , $T_j = 25^\circ\text{C}$	—	13	50	mV
Load regulation	REG_{L}	$I_O = 1$ to 300mA , $T_j = 25^\circ\text{C}$	—	30	300	mV
		$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	10	150	mV
Bias current	I_{Bias}	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias(IN)}}$	$V_I = -21$ to -33V , $T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias(L)}}$	$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	450	—	μV
Ripple rejection ratio	RR	$V_I = -22$ to -32V , $I_O = 50\text{mA}$, $f = 120\text{Hz}$	55	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$I_O = 200\text{mA}$, $T_j = 25^\circ\text{C}$	—	1.1	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_I = -35\text{V}$, $T_j = 25^\circ\text{C}$	—	10	—	mA
Peak output current	$I_{\text{O(Peak)}}$	$T_j = 25^\circ\text{C}$	—	500	—	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5\text{mA}$	—	–1	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = -27\text{V}$, $I_O = 100\text{mA}$, $C_1 = 2\mu\text{F}$, $C_O = 1\mu\text{F}$ and $T_j = 0$ to 125°C

• AN79N20 (–20V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	–19.2	–20	–20.8	V
Output voltage tolerance	V_O	$V_I = -23$ to -35V , $I_O = 5$ to 200mA	–19	—	–21	V
Line regulation	REG_{IN}	$V_I = -23$ to -35V , $T_j = 25^\circ\text{C}$	—	19	80	mV
		$V_I = -24$ to -34V , $T_j = 25^\circ\text{C}$	—	14	70	mV
Load regulation	REG_{L}	$I_O = 1$ to 300mA , $T_j = 25^\circ\text{C}$	—	30	300	mV
		$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	10	150	mV
Bias current	I_{Bias}	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias(IN)}}$	$V_I = -23$ to -35V , $T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias(L)}}$	$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	500	—	μV
Ripple rejection ratio	RR	$V_I = -24$ to -34V , $I_O = 50\text{mA}$, $f = 120\text{Hz}$	54	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$I_O = 200\text{mA}$, $T_j = 25^\circ\text{C}$	—	1.1	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_I = -35\text{V}$, $T_j = 25^\circ\text{C}$	—	10	—	mA
Peak output current	$I_{\text{O(Peak)}}$	$T_j = 25^\circ\text{C}$	—	500	—	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5\text{mA}$	—	–1	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = -29\text{V}$, $I_O = 100\text{mA}$, $C_1 = 2\mu\text{F}$, $C_O = 1\mu\text{F}$ and $T_j = 0$ to 125°C

■ Electrical Characteristics at $T_a = 25^\circ\text{C}$ (continued)

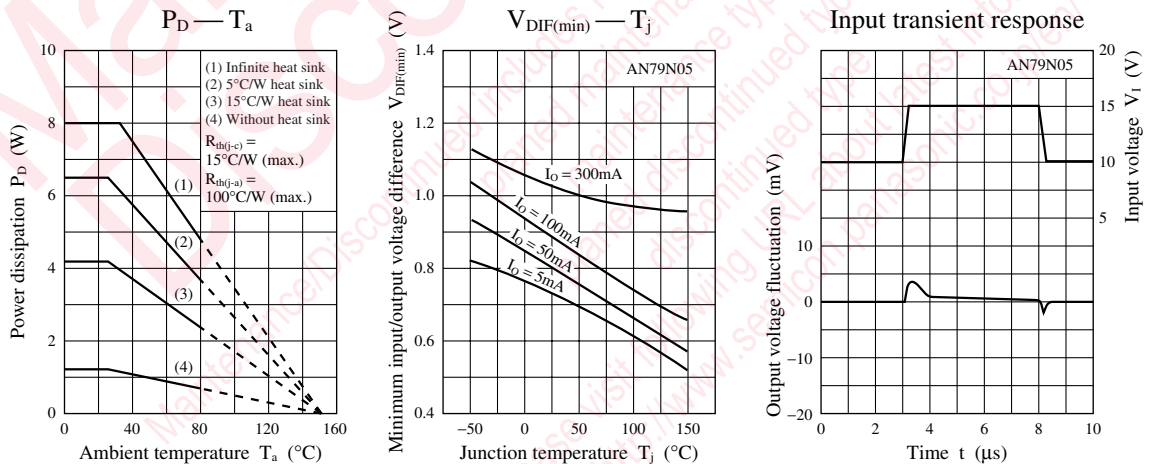
• AN79N24 (-24V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	-23	-24	-25	V
Output voltage tolerance	V_O	$V_I = -27$ to -38V , $I_O = 5$ to 200mA	-22.8	—	-25.2	V
Line regulation	REG_{IN}	$V_I = -27$ to -38V , $T_j = 25^\circ\text{C}$	—	20	80	mV
		$V_I = -27$ to -37V , $T_j = 25^\circ\text{C}$	—	15	70	mV
Load regulation	REG_{L}	$I_O = 1$ to 300mA , $T_j = 25^\circ\text{C}$	—	30	300	mV
		$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	10	150	mV
Bias current	I_{Bias}	$T_j = 25^\circ\text{C}$	—	3	5	mA
Bias current fluctuation to input	$\Delta I_{\text{Bias(IN)}}$	$V_I = -27$ to -38V , $T_j = 25^\circ\text{C}$	—	—	0.5	mA
Bias current fluctuation to load	$\Delta I_{\text{Bias(L)}}$	$I_O = 5$ to 200mA , $T_j = 25^\circ\text{C}$	—	—	0.1	mA
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	600	—	μV
Ripple rejection ratio	RR	$V_I = -28$ to -38V , $I_O = 50\text{mA}$, $f = 120\text{Hz}$	54	—	—	dB
Minimum input/output voltage difference	$V_{\text{DIF(min)}}$	$I_O = 200\text{mA}$, $T_j = 25^\circ\text{C}$	—	1.1	—	V
Output short-circuit current	$I_{\text{O(Short)}}$	$V_I = -35\text{V}$, $T_j = 25^\circ\text{C}$	—	10	—	mA
Peak output current	$I_{\text{O(Peak)}}$	$T_j = 25^\circ\text{C}$	—	500	—	mA
Output voltage temperature coefficient	$\Delta V_O/T_a$	$I_O = 5\text{mA}$	—	-1	—	$\text{mV}/^\circ\text{C}$

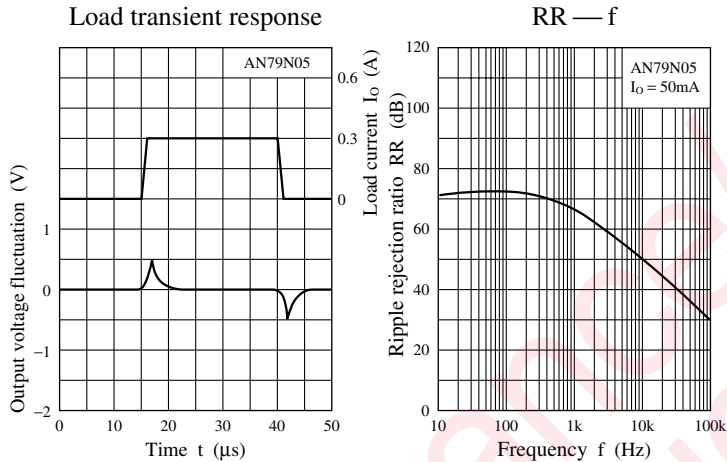
Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = -33\text{V}$, $I_O = 100\text{mA}$, $C_1 = 2\mu\text{F}$, $C_O = 1\mu\text{F}$ and $T_j = 0$ to 125°C

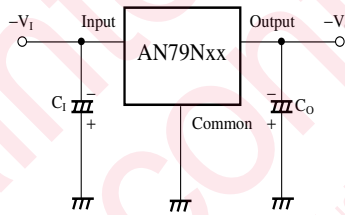
■ Main Characteristics



■ Main Characteristics (continued)



■ Basic Regulator Circuit



Connect C_1 of $2\mu\text{F}$ when the input line is long.
 C_0 improves the transient response. $1\mu\text{F}$

■ Usage Notes

1. Cautions for a basic circuit

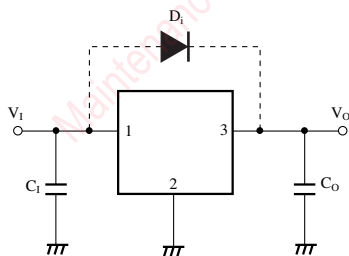


Figure 1

C_1 : When a wiring from a smoothing circuit to a three-pin regulator is long, it is likely to oscillate at output. A capacitor of $0.1\mu\text{F}$ to $0.47\mu\text{F}$ should be connected near an input pin.

C_0 : Deadly needed to prevent from oscillation ($0.33\mu\text{F}$ to $1.0\mu\text{F}$). It is recommended to use a capacitor of a small internal impedance (ex. tantalum capacitor) when using it under a low temperature.

When any sudden change of load current is likely to occur, connect an electrolytic capacitor of $10\mu\text{F}$ to $100\mu\text{F}$ to improve a transitional response of output voltage.

D_1 : Normally unnecessary. But add it in the case that there is a residual voltage at the output capacitor C_0 even after switching off the supply power because a current is likely to flow into an output pin of the IC and damage the IC.

■ Usage Notes (continued)

2. Other caution items

1) Short-circuit between the input pin and GND pin

If the input pin is short-circuited to GND or is cut off when a large capacitance capacitor has been connected to the IC's load, a voltage of a capacitor connected to an output pin is applied between input/output of the IC and this likely results in damage of the IC. It is necessary, therefore, to connect a diode, as shown in figure 2, to counter the reverse bias between input/output pins.

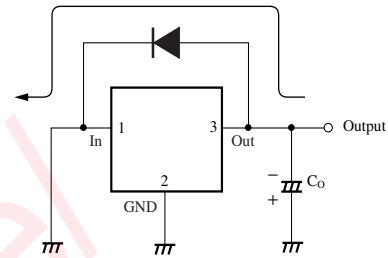
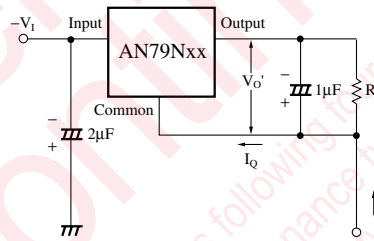


Figure 2

2) Floating of GND pin

If a GND pin is made floating in an operating mode, an unstabilized input voltage is outputted. In this case, a thermal protection circuit inside the IC does not normally operate. In this state, if the load is short-circuited or overloaded, it is likely to damage the IC.

■ Application Circuit Example



$$|I_0| = \frac{V_0'}{R} + I_Q$$

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